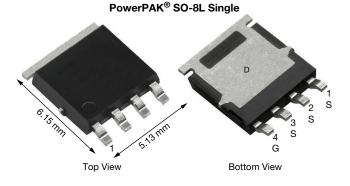
SQJ416EP



Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	100
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.030
I _D (A)	27
Configuration	Single
Package	PowerPAK SO-8L



FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

N-Channel MOSFET



KOHS COMPLIANT HALOGEN FREE

PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	100	N/		
Gate-Source Voltage		V _{GS}	± 20	V		
Continuous Drain Current	T _C = 25 °C	1	27	A		
Continuous Drain Current	T _C = 125 °C	I _D	15			
Continuous Source Current (Diode Conduct	ion) ^a	I _S	30			
Pulsed Drain Current ^b		I _{DM}	70			
Single Pulse Avalanche Current		I _{AS}	23			
Single Pulse Avalanche Energy L = 0.1 m		E _{AS}	26	mJ		
Maximum Dawar Dissinction b	T _C = 25 °C	P	45	W		
Maximum Power Dissipation ^b	T _C = 125 °C	P _D	15			
Operating Junction and Storage Temperatur	re Range	T _J , T _{stg}	-55 to +175	°C		
Soldering Recommendations (Peak Temperations		260	Ĵ			

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	70	°C/W
Junction-to-Case (Drain)		R _{thJC}	3.3	0/14

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static					•	•		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	100	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{V}_{\text{GS}} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.022	0.030	± 100 nA 1 μA 50 μA 150 Ω 0.030 Ω 0.050 Ω 0.063 Ω 0.063 P 800 P 800 P 40 P 20 P 40 Ω 3.2 Ω 10 35 ns	
Drain-Source On-State Resistance ^a		$V_{GS} = 10 V$	I _D = 10 A, T _J = 125 °C	-	-	0.050		
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.063		
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 10 A	-	22	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	580	800		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 V$, f = 1 MHz	-	400	550	pF	
Reverse Transfer Capacitance	C _{rss}			-	24	40		
Total Gate Charge ^c	Qg			-	10	20		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 50 \text{ V}, I_{D} = 10 \text{ A}$	-	3	-	nC	
Gate-Drain Charge ^c	Q _{gd}	1		-	3	-		
Gate Resistance	R _g	f = 1 MHz		1	2.1	3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	6	10		
Rise Time ^c	tr		$V_{DD} = 50 \text{ V}, \text{ R}_{\text{I}} = 10 \Omega$		20	35		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 5 A,$	$V_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$	-	11	20	ns	
Fall Time ^c	t _f	1		-	20	35	1	
Source-Drain Diode Ratings and Chara	acteristics ^b	·						
Pulsed Current ^a	I _{SM}			-	-	70	Α	
		1	= 10 A, V _{GS} = 0		0.87	1.2	V	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

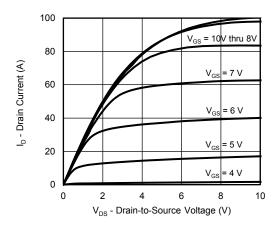
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

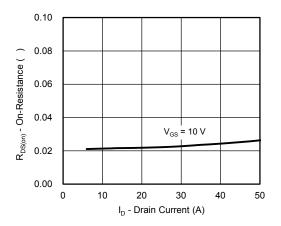
2



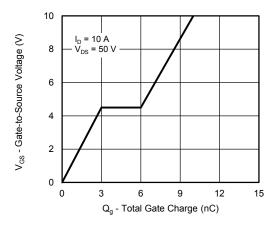
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



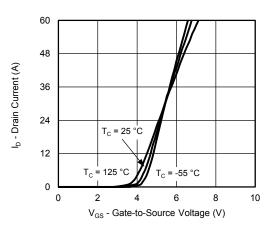
Output Characteristics



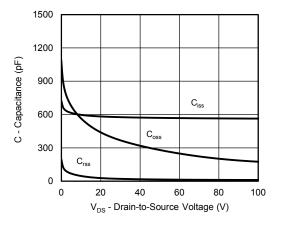
On-Resistance vs. Drain Current



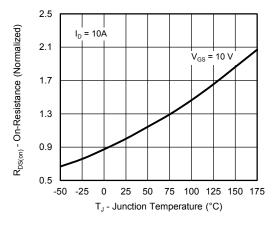
Gate Charge



Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature

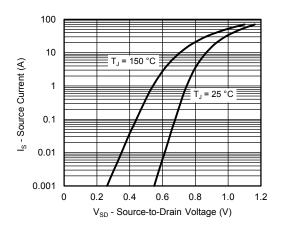
S16-0422-Rev. B, 14-Mar-16

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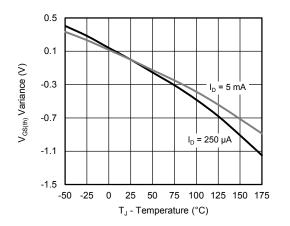
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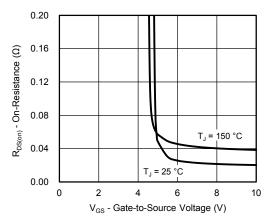
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



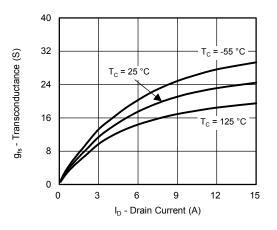
Source Drain Diode Forward Voltage

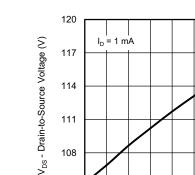


Threshold Voltage



On-Resistance vs. Gate-to Source Voltage





111

108

105

-50 -25

0

Transconductance

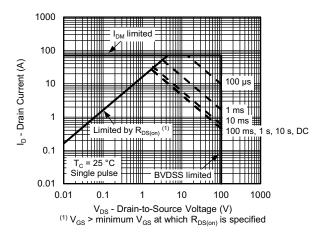
T_J - Junction Temperature (°C)

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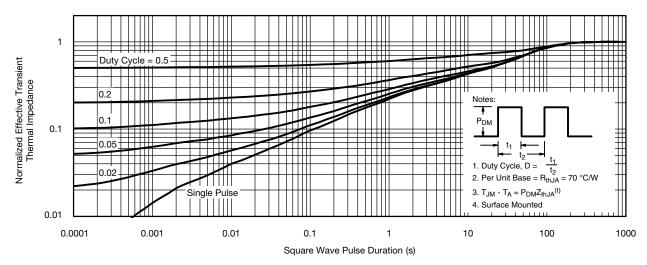
25 50 75 100 125 150 175



TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



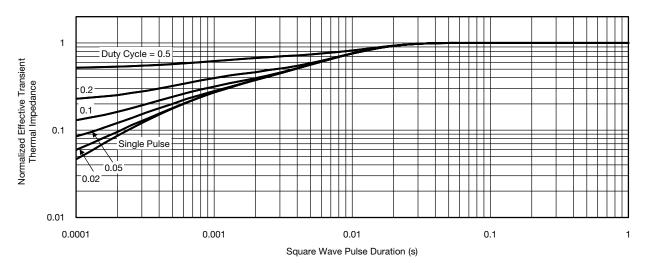
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75967.



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REVISION HISTORY^a

REVISION	DATE	DESCRIPTION OF CHANGE
В	25-Feb-16	Standardized switching and gate charge test conditions

Note

a. As of April 2014









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Package Information



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DIM.	MILLIMETERS			INCHES				
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094		0.004				
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC			0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К		0.51			0.020			
W		0.23			0.009			
W1	0.41			0.016				
W2	2.82			0.111				
W3		2.96			0.117			
θ	0°	-	10°	0°	-	10°		

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

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